



## Welcome to IEEE Xplore™

- ☐ Home
- ☐ What Can I Access?
- ☐ Log-out

## Tables of Contents

- ☐ Journals & Magazines
- ☐ Conference Proceedings
- ☐ Standards

## Search

- ☐ By Author
- ☐ Basic
- ☐ Advanced

## Member Services

- ☐ Join IEEE
- ☐ Establish IEEE Web Account

Print Format

Your search matched **26** of **764280** documents.  
Results are shown **25** a page, sorted by **publication year** in **descending** order.  
You may refine your search by editing the current search expression or entering a new one the text box.  
Then click **Search Again**.

**Search Again****Results:**Journal or Magazine = **JNL** Conference = **CNF** Standard = **STD****1 Local iterative Monte Carlo analysis of electron-electron interaction in short-channel Si-MOSFETs***Mietzner, T.; Jakumeit, J.; Ravaioli, U.*

Electron Devices, IEEE Transactions on , Volume: 48 Issue: 10 , Oct. 2001

Page(s): 2323 -2330

[\[Abstract\]](#) [\[PDF Full-Text \(200 KB\)\]](#) **JNL****2 Hot carrier induced degradation in mesa-isolated n-channel SOI MOSFETs operating in a Bi-MOS mode***Ru Huang; Jinyan Wang; Xing Zhang; Yangyuan Wang*

Electron Devices, IEEE Transactions on , Volume: 48 Issue: 8 , Aug. 2001

Page(s): 1594 -1598

[\[Abstract\]](#) [\[PDF Full-Text \(120 KB\)\]](#) **JNL****3 Antimony assisted arsenic S/D extension (A/sup 3/ SDE) engineering for sub-0.1 /spl mu/m nMOSFETs : a novel approach to steep and retrograde indium pocket profiles***Jiang, H.C.-H.; Wang, C.-C.; Hsieh, C.-H.; Lu, S.-Y.; Chiang, M.-C.; Chu, Y.-L.; Chen, C.-J.; Ong, T.-C.; Tahui Wang; Griffin, P.B.; Diaz, C.H.*

Electron Devices Meeting, 2001. IEDM Technical Digest. International , 2001

Page(s): 3.4.1 -3.4.4

[\[Abstract\]](#) [\[PDF Full-Text \(292 KB\)\]](#) **CNF****4 Hot-carrier effects and reliable lifetime prediction in deep submicron N- and P-channel SOI MOSFETs***Shing-Hwa Renn; Pelloie, J.-L.; Balestra, F.*

Electron Devices, IEEE Transactions on , Volume: 45 Issue: 11 , Nov. 1998

Page(s): 2335 -2342

[\[Abstract\]](#) [\[PDF Full-Text \(268 KB\)\]](#) **JNL**

---

**5 A thorough investigation of the degradation induced by hot-carrier injection in deep submicron N- and P-channel partially and fully depleted unibond and SIMOX MOSFETs**

*Shing-Hwa Renn; Raynaud, C.; Pelloie, J.-L.; Balestra, F.*

Electron Devices, IEEE Transactions on , Volume: 45 Issue: 10 , Oct. 1998

Page(s): 2146 -2152

[\[Abstract\]](#) [\[PDF Full-Text \(268 KB\)\]](#) **JNL**

---

**6 Hot-carrier effects and lifetime prediction in off-state operation of deep submicron SOI N-MOSFETs**

*Shing-Hwa Renn; Raully, E.; Pelloie, J.-L.; Balestra, F.*

Electron Devices, IEEE Transactions on , Volume: 45 Issue: 5 , May 1998

Page(s): 1140 -1146

[\[Abstract\]](#) [\[PDF Full-Text \(248 KB\)\]](#) **JNL**

---

**7 Hot electron induced punchthrough (HEIP) in p-channel SOI MOSFET's**

*Zhao, X.; Ioannou, D.E.; Jenkins, W.C.; Hughes, H.L.; Liu, S.T.*

SOI Conference, 1998. Proceedings., 1998 IEEE International , 1998

Page(s): 83 -84

[\[Abstract\]](#) [\[PDF Full-Text \(196 KB\)\]](#) **CNF**

---

**8 Comparison of hot-carrier effects in deep submicron N- and P-channel partially- and fully-depleted Unibond and SIMOX MOSFETs**

*Renn, S.H.; Raynaud, C.; Pelloie, J.L.; Balestra, F.*

Reliability Physics Symposium Proceedings, 1998. 36th Annual. 1998 IEEE International , 1998

Page(s): 203 -208

[\[Abstract\]](#) [\[PDF Full-Text \(676 KB\)\]](#) **CNF**

---

**9 Photon emission in deep submicrometre N-channel SOI MOSFETs**

*Renn, S.H.; Pelloie, J.L.; Balestra, F.*

Electronics Letters , Volume: 33 Issue: 12 , 5 June 1997

Page(s): 1093 -1094

[\[Abstract\]](#) [\[PDF Full-Text \(216 KB\)\]](#) **JNL**

---

**10 A method for the prediction of hot-carrier lifetime in floating SOI NMOSFETs**

*Maeda, S.; Yamaguchi, Y.; Il-Jung Kim; Joachim, H.-O.; Inoue, Y.; Miyoshi, H.; Yasuoka, A.*

Electron Devices, IEEE Transactions on , Volume: 44 Issue: 12 , Dec. 1997

Page(s): 2200 -2206

[\[Abstract\]](#) [\[PDF Full-Text \(168 KB\)\]](#) **JNL**

---

**11 In-circuit hot-carrier model and its application to inverter chain optimization**

*Horiuchi, T.*

Electron Devices, IEEE Transactions on , Volume: 43 Issue: 9 , Sept. 1996

Page(s): 1428 -1432

[\[Abstract\]](#) [\[PDF Full-Text \(448 KB\)\]](#) **JNL**

---

**12 Hot-carrier effects in deep submicron thin film SOI MOSFETs**

*Renn, S.H.; Pelloie, J.L.; Balestra, F.*

Electron Devices Meeting, 1996., International , 1996

Page(s): 877 -880

[\[Abstract\]](#) [\[PDF Full-Text \(340 KB\)\]](#) **CNF**

---

**13 Hot-carrier effects in deep submicron SOI MOSFETs**

*Renn, S.H.; Pelloie, J.L.; Balestra, F.*

SOI Conference, 1996. Proceedings., 1996 IEEE International , 1996

Page(s): 60 -61

[\[Abstract\]](#) [\[PDF Full-Text \(200 KB\)\]](#) **CNF**

---

**14 A study on hot carrier effects on N-MOSFETs under high substrate impurity concentration**

*Ono, M.; Saito, M.; Yoshitomi, T.; Fiegna, C.; Ohguro, T.; Momose, H.S.; Iwai, H.*

Electron Devices, IEEE Transactions on , Volume: 42 Issue: 8 , Aug. 1995

Page(s): 1510 -1521

[\[Abstract\]](#) [\[PDF Full-Text \(836 KB\)\]](#) **JNL**

---

**15 Hot-carrier effects on gate-induced-drain-leakage (GIDL) current in thin-film SOI/NMOSFET's**

*Binglong Zhang; Balasinski, A.; Ma, T.P.*

IEEE Electron Device Letters , Volume: 15 Issue: 5 , May 1994

Page(s): 169 -171

[\[Abstract\]](#) [\[PDF Full-Text \(232 KB\)\]](#) [JNL](#)

---

**16 Hot carrier effects in n-channel polycrystalline silicon thin-film transistors: a correlation between off-current and transconductance variations**

*Fortunato, G.; Pecora, A.; Tallarida, G.; Mariucci, L.; Reita, C.; Migliorato, P.*

Electron Devices, IEEE Transactions on , Volume: 41 Issue: 3 , March 1994

Page(s): 340 -346

[\[Abstract\]](#) [\[PDF Full-Text \(604 KB\)\]](#) [JNL](#)

---

**17 Improved hot-carrier immunity in CMOS analog device with N/sub 2/O-nitrided gate oxides**

*Lo, G.Q.; Ahn, J.; Kwong, D.-L.*

IEEE Electron Device Letters , Volume: 13 Issue: 9 , Sept. 1992

Page(s): 457 -459

[\[Abstract\]](#) [\[PDF Full-Text \(248 KB\)\]](#) [JNL](#)

---

**18 AC hot-carrier effects in MOSFETs with furnace N/sub 2/O-nitrided gate oxides**

*Lo, G.Q.; Ahn, J.; Kwong, D.-L.*

IEEE Electron Device Letters , Volume: 13 Issue: 6 , June 1992

Page(s): 341 -343

[\[Abstract\]](#) [\[PDF Full-Text \(244 KB\)\]](#) [JNL](#)

---

**19 Hot-carrier effects in MOSFET's with nitrided-oxide gate-dielectrics prepared by rapid thermal processing**

*Hori, T.; Yasui, T.; Akamatsu, S.*

Electron Devices, IEEE Transactions on , Volume: 39 Issue: 1 , Jan. 1992

Page(s): 134 -147

[\[Abstract\]](#) [\[PDF Full-Text \(1272 KB\)\]](#) [JNL](#)

---

**20 Hot-carrier effects in 0.1 mu m gate length CMOS devices**

*Mizuno, T.; Toriumi, A.; Iwase, M.; Takahashi, M.; Niiyama, H.; Fukmoto, M.; Yoshimi, M.*

Electron Devices Meeting, 1992. Technical Digest., International , 1992

Page(s): 695 -698

[\[Abstract\]](#) [\[PDF Full-Text \(340 KB\)\]](#) **CNF**

---

**21 Performance and reliability design issues for deep-submicrometer CMOSFETs**

*Chung, J.E.; Jeng, M.-C.; Moon, J.E.; Ko, P.-K.; Hu, C.*

Electron Devices, IEEE Transactions on , Volume: 38 Issue: 3 , March 1991

Page(s): 545 -554

---

[\[Abstract\]](#) [\[PDF Full-Text \(936 KB\)\]](#) **JNL**

---

**22 New detection method of hot-carrier degradation using photon spectrum analysis of weak luminescence on CMOS VLSI**

*Tsutsu, N.; Uraoka, Y.; Nakata, Y.; Akiyama, S.; Esaki, H.*

Microelectronic Test Structures, 1990. ICMTS 1990. Proceedings of the 1990 International Conference on , 1990

Page(s): 143 -148

---

[\[Abstract\]](#) [\[PDF Full-Text \(328 KB\)\]](#) **CNF**

---

**23 Computer simulation of hot-carrier effects in asymmetric LDD and LDS MOSFET devices**

*Chen, Y.-Z.; Tang, T.-W.*

Electron Devices, IEEE Transactions on , Volume: 36 Issue: 11 Part: 2 , Nov. 1989

Page(s): 2492 -2498

---

[\[Abstract\]](#) [\[PDF Full-Text \(580 KB\)\]](#) **JNL**

---

**24 Hot-carrier effects in n-channel MOS transistors under alternating stress conditions**

*Bellens, R.; Heremans, P.; Groeseneken, G.; Maes, H.E.*

IEEE Electron Device Letters , Volume: 9 Issue: 5 , May 1988

Page(s): 232 -234

---

[\[Abstract\]](#) [\[PDF Full-Text \(220 KB\)\]](#) **JNL**

---

**25 A band to band tunneling MOS device (B/sup 2/T-MOSFET)-a kind of 'Si quantum device'**

*Takeda, E.; Matsuoka, H.; Igura, Y.; Asai, S.*

Electron Devices Meeting, 1988. Technical Digest., International , 1988

Page(s): 402 -405

[\[Abstract\]](#)   [\[PDF Full-Text \(176 KB\)\]](#)   **CNF**

---

1 2 [\[Next\]](#)

[Home](#) | [Log-out](#) | [Journals](#) | [Conference Proceedings](#) | [Standards](#) | [Search by Author](#) | [Basic Search](#) | [Advanced Search](#)  
[Join IEEE](#) | [Web Account](#) | [New this week](#) | [OPAC Linking Information](#) | [Your Feedback](#) | [Technical Support](#) | [Email Alerting](#)  
[No Robots Please](#) | [Release Notes](#) | [IEEE Online Publications](#) | [Help](#) | [FAQ](#) | [Terms](#) | [Back to Top](#)

Copyright © 2002 IEEE — All rights reserved